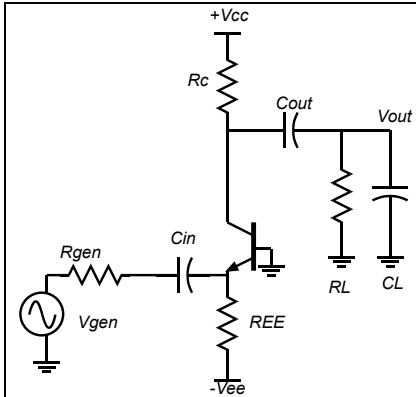


	<p>Problem 1.</p> $V_{out}(s)/V_{in}(s) = c \frac{1 + b_1 s^2 + b_2 s^2 + \dots}{1 + a_1 s^2 + a_2 s^2 + \dots}$ <p>$R_1=1 \text{ k}\Omega$, $R_2=2 \text{ k}\Omega$, $R_3=3 \text{ k}\Omega$, $R_4=4 \text{ k}\Omega$ $C_1=1 \text{ fF}$ $C_2=2 \text{ fF}$ Find a_1 and a_2 (give units!). Find, approximately, the 2 dominant pole frequencies of the transfer function. HINT: USE MOTC !</p>
	<p>Problem 2.</p> <p>The transistor has $\tau_f=1 \text{ ps}$, $C_{je}=C_{cb}=5 \text{ fF}$. β is 100. V_{cc} and V_{ee} are $\pm 3 \text{ volts}$. $R_L=200 \text{ }\Omega$, $C_L=200 \text{ fF}$. $R_b=10 \cdot R_{gen}$, $R_{gen}=1 \text{ k}\Omega$. Choose R_{EE} to bias the transistor at 5 mA.</p> <p>a) Find bias conditions, mid-band V_{out}/V_{in}, V_{in}/V_{gen}, R_{out_amp}, R_{in_amp} b) USE MOTC to find a_1 and a_2 of the transfer function. Find the dominant poles: are they real or complex ? c) Draw a Bode Magnitude plot of the transfer function V_{out}/V_{gen}. What is the 3 dB bandwidth ?</p>
	<p>Problem 3.</p> <p>The NMOS FET $K_\mu = 10 \text{ mA/V}^2 \cdot (W_g / 1 \mu\text{m})$ $K_n = 2.0 \text{ mA/V} \cdot (W_g / 1 \mu\text{m})$ $\Delta V = 0.1 \text{ V}$, $1/\lambda = 4$ Volts, and a 0.25 V threshold. $L_g = 30 \text{ nm}$ The gate-source capacitance C_{gs} is $(20 \text{ fF} / (\mu\text{m})^2) \cdot L_g W_g + (0.5 \text{ fF} / \mu\text{m}) \cdot W_g$ while C_{gd} is $(0.5 \text{ fF} / \mu\text{m}) \cdot W_g$.</p> <p>We will bias the device at 1 mA drain current, and pick a gate width such that the FET V_{gs} is 0.3 Volts. The supplies are $+0 \text{ V}$ and -3.0 V. $R_{gen}=200 \text{ k}\Omega$. R_L is $1000 \text{ }\Omega$ and C_L is 100 fF.</p> <p>a) Find R_{ss}, the bias conditions, mid-band V_{out}/V_{in}, V_{in}/V_{gen}, R_{out_amp}, R_{in_amp}, the device capacitances, and the transistor ft. b) USE MOTC to find a_1 and a_2 of the transfer function. Find the dominant poles: are they real or complex ? c) Draw a Bode Magnitude plot of the transfer function V_{out}/V_{gen}. What is the 3 dB bandwidth ?</p>



Problem 4.

The transistor has $\tau_f=0.5$ ps, $C_{je}=10$ fF and $C_{cb}=25$ fF. β is 100. V_{cc} and V_{ee} are ± 3.3 volts. $R_L=600$ Ohm, $C_L=50$ fF. $R_{gen}=100$ Ohm.

Choose R_{EE} to bias the transistor at 1mA, choose R_c to bias the transistor with $V_{ce}=2.0$ volts

- Find bias conditions, mid-band V_{out}/V_{in} , V_{in}/V_{gen} , R_{out_amp} , R_{in_amp}
- any method you like find a_1 and a_2 of the transfer function. Find the dominant poles frequencies.
- Draw a Bode Magnitude plot of the transfer function V_{out}/V_{gen} . What is the 3 dB bandwidth ?